TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N-CHANNEL IGBT

GT40M101

HIGH POWER SWITCHING APPLICATIONS

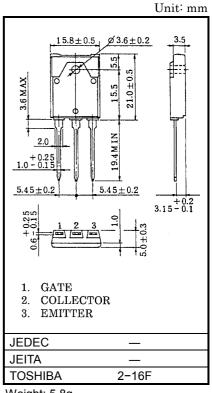
• High Input Impedance

High Speed $t_f = 0.4 \mu s \text{ (Max.)}$ Low Saturation Voltage $: V_{CE(sat)} = 3.4V \text{ (Max.)}$

Enhancement-Mode

MAXIMUM RATINGS (Ta = 25°C)

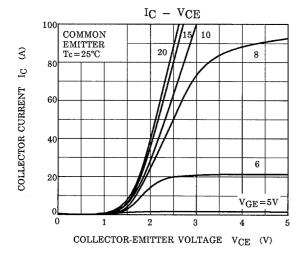
CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	900	V	
Gate-Emitter Voltage		V_{GES}	±25	V	
Collector Current	DC	Ic	40	А	
	1ms	I _{CP}	80		
Collector Power Dissipation (Tc = 25°C)		P _C	90	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	-55~150	°C	
Screw Torque		_	0.8	N·m	

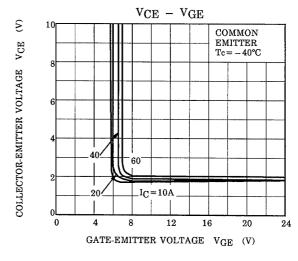


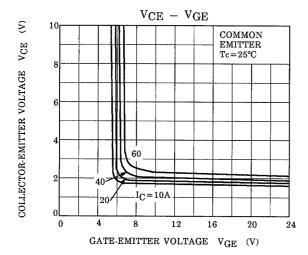
Weight: 5.8g

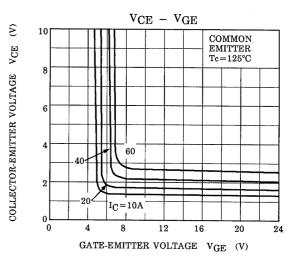
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

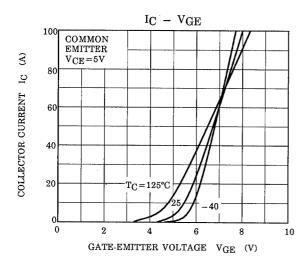
CHARA	CTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Curr	ent	I _{GES}	V _{GE} = ±25V, V _{CE} = 0	_	_	±500	nA
Collector Cut-off C	urrent	I _{CES}	V _{CE} = 900V, V _{GE} = 0	_	_	1.0	mA
Gate-Emitter Cut-o	off Voltage	V _{GE(OFF)}	I _C = 40mA, V _{CE} = 5V	3.0	_	6.0	V
Collector-Emitter S	aturation Voltage	V _{CE(sat)}	I _C = 40A, V _{GE} = 15V	_	2.1	3.4	V
Input Capacitance		C _{ies}	V _{CE} = 30V, V _{GE} = 0, f = 1MHz	_	2100	_	pF
Switching Time	Rise Time	t _r	$^{15V}_{0}$ $^{-15V}_{VCC}$ $^{62\Omega}_{VCC}$ $^{62\Omega}_{CC}$	_	0.30	_	- µs
	Turn-On Time	t _{on}		_	0.40	_	
	Fall Time	t _f		_	0.25	0.40	
	Turn-Off Time	t _{off}		_	0.60	_	
Thermal Resistance	e	R _{th(j-c)}	_	_	_	1.39	°C/W

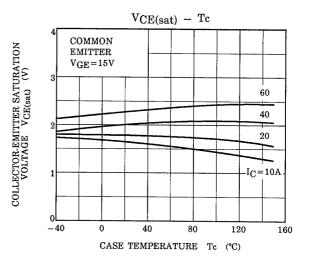




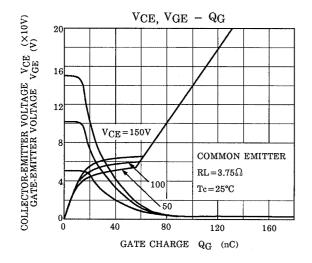


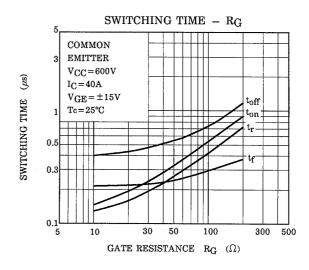


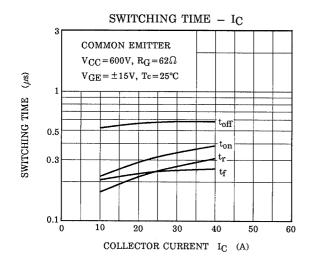


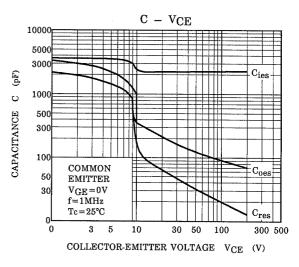


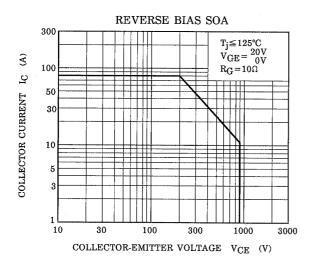
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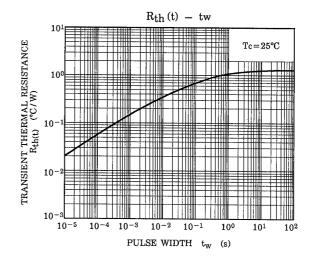




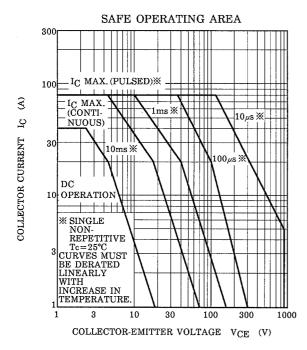








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